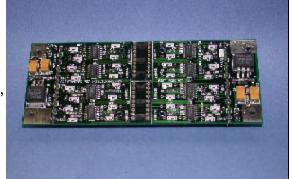
PHOTONIC 32 CHANNEL DETECTOR PRE-AMP BOARD ASSEMBLY **DETECTORS INC.** Type PDB-707-100-XX

CAUTION: ESD SENSITIVE DEVICE

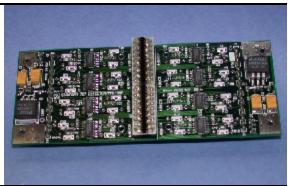
DESCRIPTION

PDB-707-100-XX This 32 channel Pre-Amplifier Board Assembly (PABA) is a side-by-side stackable platform with built-in voltage regulators, and eight precision CMOS quad op-amps. Low offset voltages and input bias currents, enhance operational stability at high voltage gains. Standard one meg feedback resistors produce a 1 KHz bandwidth, with optional selected resistors available. The following options can be used with this PABA.



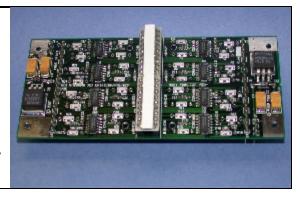
DESCRIPTION - OPTION D

PDB-707-100-D This option is designed to use two 16 element, blue enhanced silicon photodiode arrays. The arrays are on .062 [1.27] pitch with .010 [0.25] gaps. Each element is 2.51 mm² in size. The low leakage, high shunt detectors match up well with the CMOS op-amps on the PABA. This version can be used for optical color sorters, food processing, inspection equipment, optical scanners, and other multi-element photodiode array applications.



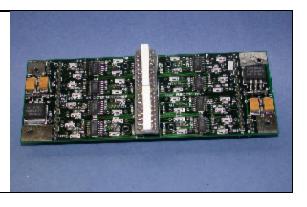
DESCRIPTION - OPTION DS

PDB-707-100-DS This option is designed to use two PDB-C216S, 16 element, blue enhanced silicon photodiode arrays, with X-ray fluoroscopic screens. The ZnCdS:Ag phosphorus doped screen emission spectrum is 530 nm (green). X-ray absorbtion is 9.66/26.7 KeV, with an effective atomic number of 38.4. This version is ideal for X-ray package inspection, diagnostic fluoroscopy and PCB examination.

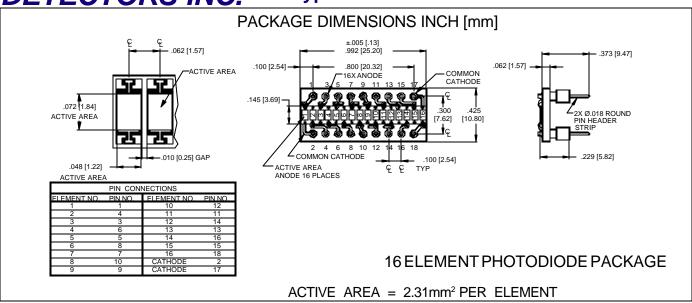


DESCRIPTION-OPTION DC

PDB-707-100-DC This option is designed to use two PDB-C216C, 16 element, blue enhanced silicon photodiode arrays, with cesium iodide thallium doped CsI (Ti), X-ray scintillation crystals. These arrays are used in 40 KeV to 120 Kev X-ray applications. Other uses include medical CT, baggage scanners, food processing and X-ray package inspection scanners.



PHOTONIC 32 CHANNEL DETECTOR PRE-AMP BOARD ASSEMBLY **DETECTORS INC.** Type PDB-C216-SP Used on PDB-707-100-D



FEATURES

- .062 inch centers
- Stackable
- Blue enhanced
- Low capacitance

DESCRIPTION

The **PDB-C216-SP** is a common cathode, monolithic silicon PIN photodiode 16 element array. Designed to be stacked end to end to form a line of optical pixels.

APPLICATIONS

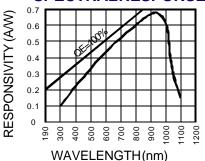
- Cardreader
- Scanners
- Characterrecognition

ABSOLUTE MAXIMUM RATING (TA=25°C unless otherwise noted)

SYMBOL	PARAMETER	MIN	MAX	UNITS
V _{BR}	Reverse Voltage		50	V
T _{STG}	Storage Temperature	-40	+100	∘C
T _o	Operating Temperature Range	-20	+75	∘C
T _s	Soldering Temperature*		+265	∘C
IL	Light Current		500	mA

^{*1/16} inch from case for 3 secs max

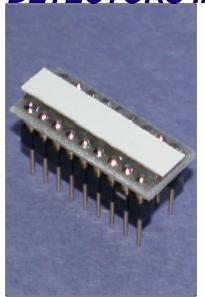
SPECTRALRESPONSE

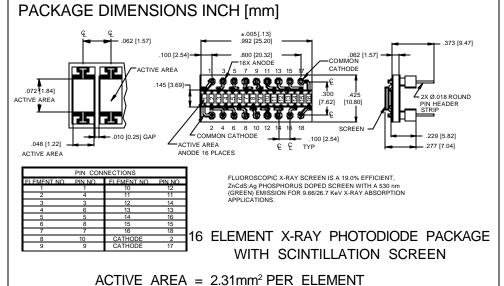


ELECTRO-OPTICAL CHARACTERISTICS (TA=25°C unless otherwise noted, without scintillator)

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	MIN	TYP	MAX	UNITS
l _{sc}	Short Circuit Current	H = 100 fc, 2850 K	18	28		μΑ
I _D	Dark Current	$H = 0, V_R = 5 V$		5	50	nA
R _{SH}	Shunt Resistance	$H = 0, V_R = 10 \text{ mV}$	100	200		МΩ
TCR _{SH}	RSH Temp. Coefficient	$H = 0, V_R = 10 \text{ mV}$		-8		%/℃
C _J	Junction Capacitance	$H = 0, V_R = 0 V^{**}$		40	60	рF
λrange	Spectral Application Range	Spot Scan	350		1100	nm
λр	Spectral Response - Peak	Spot Scan		950		nm
V _{BR}	Breakdown Voltage	I = 10 μA	15	30		V
NEP	Noise Equivalent Power	V _R = 10 V @ Peak		2x10 ⁻¹⁴		W/ √Hz
tr	Response Time	$RL = 50 \Omega V_R = 10 V$		15		nS

PHOTONIC 32 CHANNEL DETECTOR PRE-AMP BOARD ASSEMBLY DETECTORS INC. Type PDB-C216-S Used on PDB-707-100-DS





FEATURES

- .062 inch centers
- Stackable
- Scintillation screen
- Low capacitance

DESCRIPTION

The **PDB-C216-S** is a common cathode, monolithic silicon PIN photodiode 16 element array. Designed to be stacked end to end to form a line of pixels. Supplied with a fluoroscopic X-ray scintillation screen.

APPLICATIONS

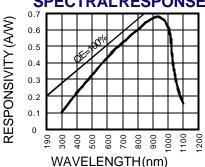
- Luggage X-ray
- X-Ray scanner
- X-Ray inspection

ABSOLUTE MAXIMUM RATING (TA=25°C unless otherwise noted)

SYMBOL	PARAMETER	MIN	MAX	UNITS
$V_{\mathtt{BR}}$	Reverse Voltage		50	V
T _{STG}	Storage Temperature	-40	+100	∘C
T _o	Operating Temperature Range	-20	+75	∘C
T _s	Soldering Temperature*		+265	∘C
IL	Light Current		500	mA

^{*1/16} inch from case for 3 secs max

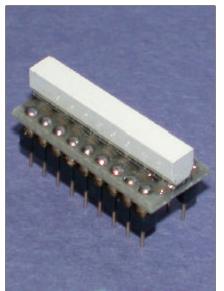
SPECTRALRESPONSE

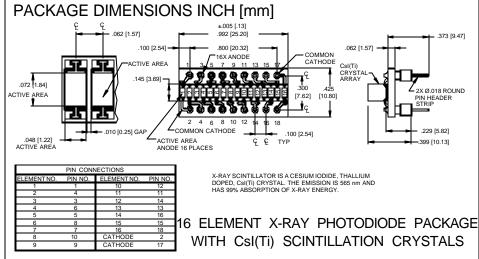


ELECTRO-OPTICAL CHARACTERISTICS (TA=25°C unless otherwise noted, without scintillator)

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	MIN	TYP	MAX	UNITS
l _{sc}	Short Circuit Current	H = 100 fc, 2850 K	18	28		μΑ
I _D	Dark Current	$H = 0, V_R = 5 V$		5	50	nA
R _{SH}	Shunt Resistance	$H = 0, V_R = 10 \text{ mV}$	100	200		MΩ
TCR _{sH}	RSH Temp. Coefficient	$H = 0, V_R = 10 \text{ mV}$		-8		%/℃
C _J	Junction Capacitance	$H = 0, V_R = 0 V^{**}$		40	60	pF
λrange	Spectral Application Range	Spot Scan	350		1100	nm
λр	Spectral Response - Peak	Spot Scan		950		nm
V _{BR}	Breakdown Voltage	Ι = 10 μιΑ	15	30		V
NEP	Noise Equivalent Power	V _R = 10 V @ Peak		2x10 ⁻¹⁴		W/ √Hz
tr	Response Time	$RL = 50 \Omega V_R = 10 V$		15		nS

PHOTONIC 32 CHANNEL DETECTOR PRE-AMP BOARD ASSEMBLY DETECTORS INC. Type PDB-C216-C Used on PDB-707-100-DC





FEATURES

- .062 inch centers
- Stackable
- Csl(Ti) crystals
- Low capacitance

DESCRIPTION

The **PDB-C216-C** is a common cathode, monolithic silicon PIN photodiode 16 element array. Designed to be stacked end to end to form a line of pixels. Supplied with X-Ray CsI(Ti) scintillation crystals.

ACTIVE AREA = 2.31mm² PER ELEMENT

APPLICATIONS

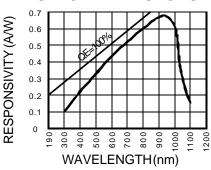
- Luggage X-ray
- X-Ray scanner
- X-Ray inspection

ABSOLUTE MAXIMUM RATING (TA=25°C unless otherwise noted)

SYMBOL	PARAMETER	MIN	MAX	UNITS
V _{BR}	Reverse Voltage		50	V
T _{STG}	Storage Temperature	-40	+100	∘C
T _o	Operating Temperature Range	-20	+75	∘C
T _s	Soldering Temperature*		+265	∘C
IL	Light Current		500	mA

^{*1/16} inch from case for 3 secs max

SPECTRALRESPONSE



ELECTRO-OPTICAL CHARACTERISTICS (TA=25°C unless otherwise noted, without scintillator)

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	MIN	TYP	MAX	UNITS
l _{sc}	Short Circuit Current	H = 100 fc, 2850 K	18	28		μΑ
I _D	Dark Current	$H = 0, V_R = 5 V$		5	50	nA
R _{SH}	Shunt Resistance	$H = 0, V_R = 10 \text{ mV}$	100	200		MΩ
TCR _{SH}	RSH Temp. Coefficient	$H = 0, V_R = 10 \text{ mV}$		-8		%/℃
C _J	Junction Capacitance	$H = 0, V_R = 0 V^{**}$		40	60	рF
λrange	Spectral Application Range	Spot Scan	350		1100	nm
λр	Spectral Response - Peak	Spot Scan		950		nm
V _{BR}	Breakdown Voltage	I = 10 µLA	15	30		V
NEP	Noise Equivalent Power	V _R = 10 V @ Peak		2x10 ⁻¹⁴		W/ √Hz
tr	Response Time	$RL = 50 \Omega V_R = 10 V$		15		nS

PHOTONIC 32 CHANNEL DETECTOR PRE-AMP BOARD ASSEMBLY **DETECTORS INC.** Type PDB-707-100-XX

AMPLIFIER SPECIFICATION PER CHANNEL TA = 25° C, V* = 5 V, V* = 0 V, V_{CM} = 1.5 V, V₀ = 2.5 V and R₁ > 1 M UNLESS OTHERWISE NOTED

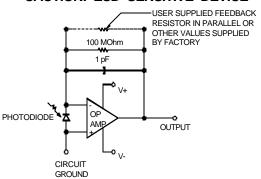
CHARACTERISTIC	TEST CONDITIONS	MIN	TYP	MAX	UNITS
INPUT OFFSET VOLTAGE (Vos)	INITIAL OFFSET		350	1000	μV
	LONGTERMOFFSETSTABILITY		15		μV/MONTH
AVERAGE INPUT OFFSET DRIFT (TCVos)	$R_L = 100 \text{ K}\Omega$		1		μV/°C
INPUT BIAS CURRENT (I₃)	OFFSETCURRENT, VCM=0			100	рА
INPUT OFFSET CURRENT (I∞)				100	рА
INPUT VOLTAGE RANGE (Iv.)	COMMON MODE REJECTION VCM±10 V	±11	±12		V
INPUT VOLTAGE NOISE (en)	VOLTAGE 0, f=100 Hz		40		nV∕√Hz
	VOLTAGE 0, f=1 Khz		30		nV∕√Hz
INPUTCURRENTNOISE (in)	TYP f=1 KHz		1.8		fA∕√Hz
FREQUENCYRESPONSE	UNITY GAIN, SMALL SIGNAL	0.8	1.0		MHz
	SLEW RATE, UNITY GAIN	1.0	1.8		V/ms
CLOSED LOOP GAIN (CLBW)	AVCL=+5 V		9		Mhz
SUPPLYCURRENT(Isy)*	V = +15 V, V ₀ = 7.5 V		27.2	32	mA
SHORT CIRCUIT CURRENT			15		mA
POWER SUPPLY	OPERATING VOLTAGE	±4.5		±15.5	V

NOTE: 8 EACH NATIONAL P/N: LMC6084, CMOS QUAD OPERATIONAL AMPLIFIER USED IN ASSEMBLY. *TOTAL ASSEMBLY SUPPLY CURRENT

AMPLIFIER ABSOLUTE MAXIMUM RATING (TA=25°C UNLESS OTHERWISE NOTED)

PARAMETER	MIN	MAX	UNITS
SUPPLYVOLTAGE		16	±V
DIFFERENTIAL INPUT VOLTAGE		±16	V
STORAGETEMPERATURE	-55	+125	°C
OPERATINGTEMPERATURE	0	+70	° C

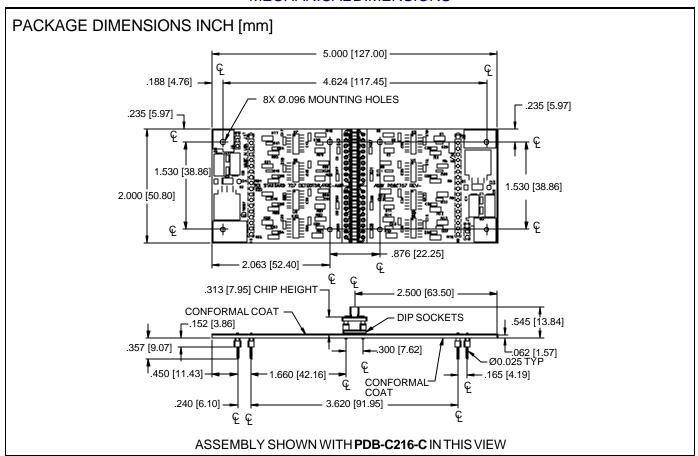
CAUTION: ESD SENSITIVE DEVICE



SINGLE OP-AMP STAGE SCHEMATIC

PHOTONIC 32 CHANNEL DETECTOR PRE-AMP BOARD ASSEMBLY DETECTORS INC.

MECHANICAL DIMENSIONS



ELECTRICAL CONNECTIONS

